

FM28V020

256Kbit Bytewise F-RAM Memory



Features

256Kbit Ferroelectric Nonvolatile RAM

- Organized as 32K x 8
- 10^{14} Read/Write Cycles
- NoDelay™ Writes
- Page Mode Operation
- Advanced High-Reliability Ferroelectric Process

Superior to Battery-backed SRAM Modules

- No battery concerns
- Monolithic reliability
- True surface mount solution, no rework steps
- Superior for moisture, shock, and vibration
- Resistant to negative voltage undershoots

SRAM Replacement

- JEDEC 32Kx8 SRAM pinout
- 70 ns Access Time, 140 ns Cycle Time

Low Power Operation

- 2.0V – 3.6V Power Supply
- Standby Current 90 μ A (typ)
- Active Current 5 mA (typ)

Industry Standard Configurations

- Industrial Temperature -40° C to +85° C
- 28-pin “Green”/RoHS SOIC (-SG)
- 28-pin “Green”/RoHS TSOP (-T28G)
- 32-pin “Green”/RoHS TSOP (-TG)

General Description

The FM28V020 is a 32K x 8 nonvolatile memory that reads and writes like a standard SRAM. A ferroelectric random access memory or F-RAM is nonvolatile, which means that data is retained after power is removed. It provides data retention for over 10 years while eliminating the reliability concerns, functional disadvantages, and system design complexities of battery-backed SRAM (BBSRAM). Fast write timing and virtually unlimited write endurance make F-RAM superior to other types of memory.

In-system operation of the FM28V020 is very similar to other RAM devices and can be used as a drop-in

replacement for standard SRAM. Read and write cycles may be triggered by /CE or simply by changing the address. The F-RAM memory is nonvolatile due to its unique ferroelectric memory process. These features make the FM28V020 ideal for nonvolatile memory applications requiring frequent or rapid writes in the form of an SRAM.

The device is available in a 28-pin SOIC, 28-pin TSOP-I, or 32-pin TSOP-I surface mount package. Device specifications are guaranteed over the industrial temperature range -40°C to +85°C.

Ordering Information	
FM28V020-SG	28-pin “Green”/RoHS SOIC
FM28V020-SGTR	28-pin “Green”/RoHS SOIC, Tape & Reel
FM28V020-T28G	28-pin “Green”/RoHS TSOP
FM28V020-T28GTR	28-pin “Green”/RoHS TSOP, Tape & Reel
FM28V020-TG	32-pin “Green”/RoHS TSOP
FM28V020-TGTR	32-pin “Green”/RoHS TSOP, Tape & Reel

This product conforms to specifications per the terms of the Ramtron standard warranty. The product has completed Ramtron’s internal qualification testing and has reached production status.

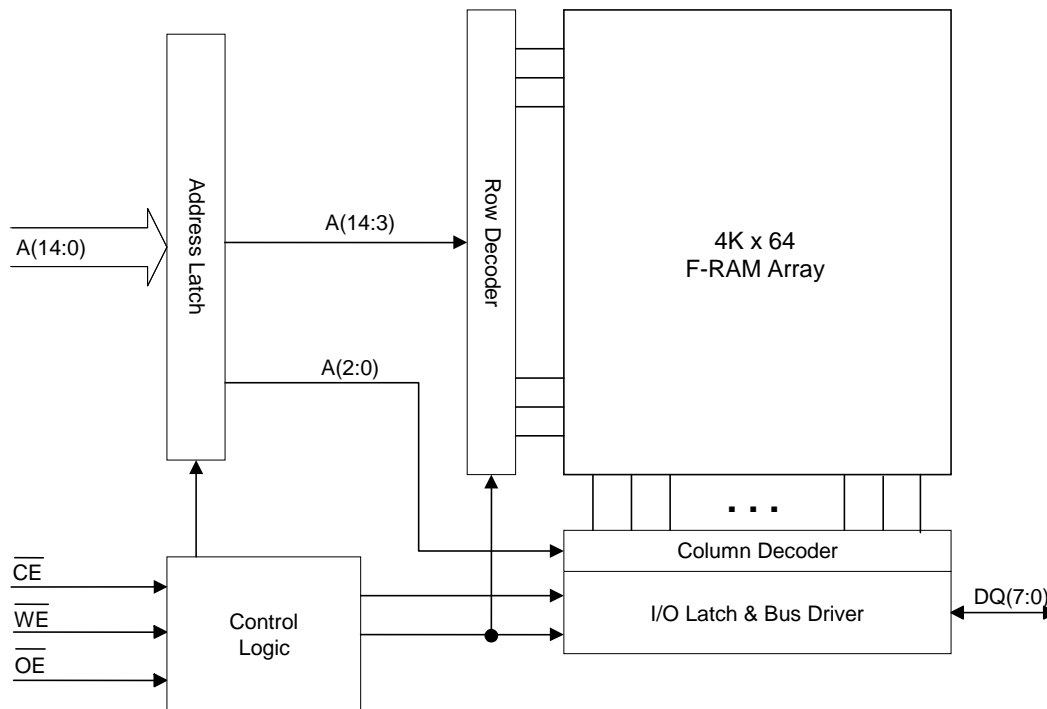


Figure 1. Block Diagram

Pin Descriptions

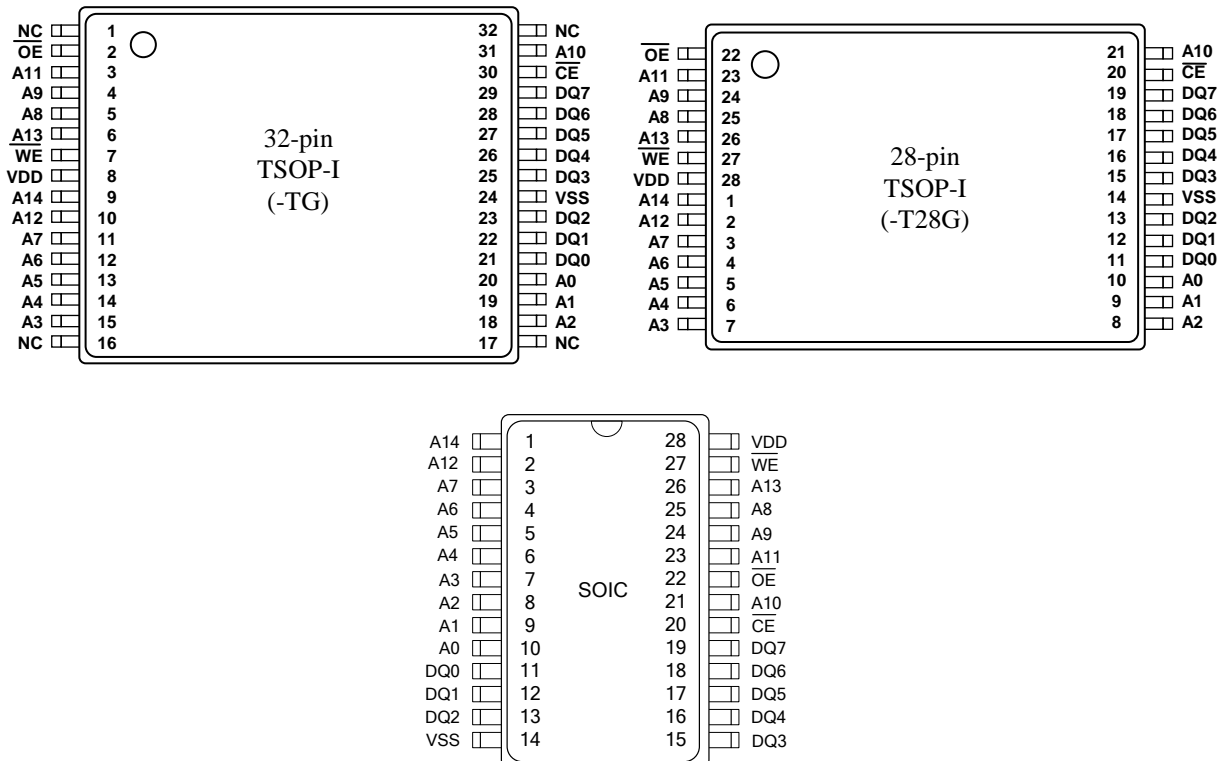
Pin Name	Type	Pin Description
A(14:0)	Input	Address inputs: The 15 address lines select one of 32,768 bytes in the F-RAM array. The address value is latched on the falling edge of /CE. Addresses A(2:0) are used for page mode read and write operations.
/CE	Input	Chip Enable input: The device is selected and a new memory access begins on the falling edge of /CE. The entire address is latched internally at this point.
/WE	Input	Write Enable: A write cycle begins when /WE is asserted. The rising edge causes the FM28V020 to write the data on the DQ bus to the F-RAM array. The falling edge of /WE latches a new column address for fast page mode write cycles.
/OE	Input	Output Enable: When /OE is low, the FM28V020 drives the data bus when valid data is available. Deasserting /OE high tri-states the DQ pins.
DQ(7:0)	I/O	Data: 8-bit bi-directional data bus for accessing the F-RAM array.
VDD	Supply	Supply Voltage
VSS	Supply	Ground

Functional Truth Table

/CE	/WE	A(14:3)	A(2:0)	Operation
H	X	X	X	Standby/Idle
↓	H	V	V	Read
L	H	No Change	Change	Page Mode Read
L	H	Change	V	Random Read
↓	L	V	V	/CE-Controlled Write ²
L	↓	V	V	/WE-Controlled Write ^{2,3}
L	↓	No Change	V	Page Mode Write ⁴
↑	X	X	X	Starts Precharge

Notes:

- 1) H=Logic High, L=Logic Low, V=Valid Address, X=Don't Care.
- 2) For write cycles, data-in is latched on the rising edge of /CE or /WE, whichever comes first.
- 3) /WE-controlled write cycle begins as a Read cycle and A(14:3) is latched then.
- 4) Addresses A(2:0) must remain stable for at least 15 ns during page mode operation.

Pin Configurations


Overview

The FM28V020 is a byte-wide F-RAM memory logically organized as 32,768 x 8 and is accessed using an industry standard parallel interface. All data written to the part is immediately nonvolatile with no delay. The device offers page mode operation which provides higher speed access to addresses within a page (row). An access to a different page is triggered by toggling the chip enable pin or simply by changing the upper address A(14:3).

Memory Operation

Users access 32,768 memory locations with 8 data bits each through a parallel interface. The F-RAM array is organized as 8 blocks each having 512 rows. Each row has 8 column locations, which allows fast access in page mode operation. Once an initial address has been latched by the falling edge of /CE, subsequent column locations may be accessed without the need to toggle the chip enable. When either chip enable pin is deasserted, a precharge operation begins. Writes occur immediately at the end of the access with no delay. The /WE pin must be toggled for each write operation.

Read Operation

A read operation begins on the falling edge of /CE. The /CE-initiated access causes the address to be latched and starts a memory read cycle if /WE is high. Data becomes available on the bus after the access time has been satisfied. Once the address has been latched and the access completed, a new access to a random location (different row) may begin while /CE is still active. The minimum cycle time for random addresses is t_{RC} . Note that unlike SRAMs, the FM28V020's /CE-initiated access time is faster than the address cycle time.

The FM28V020 will drive the data bus only when /OE is asserted low and the memory access time has been satisfied. If /OE is asserted prior to completion of the memory access, the data bus will not be driven until valid data is available. This feature minimizes supply current in the system by eliminating transients caused by invalid data being driven onto the bus. When /OE is inactive, the data bus will remain hi-Z.

Write Operation

Writes occur in the FM28V020 in the same time interval as reads. The FM28V020 supports both /CE- and /WE-controlled write cycles. In both cases, the address is latched on the falling edge of /CE.

In a CE-controlled write, the /WE signal is asserted prior to beginning the memory cycle. That is, /WE is low when the device is activated with the chip enable.

In this case, the device begins the memory cycle as a write. The FM28V020 will not drive the data bus regardless of the state of /OE as long as /WE is low. Input data must be valid when the device is deselected with the chip enable. In a /WE-controlled write, the memory cycle begins when the device is activated with the chip enable. The /WE signal falls some time later. Therefore, the memory cycle begins as a read. The data bus will be driven if /OE is low, however it will hi-Z once /WE is asserted low. The /CE- and /WE-controlled write timing cases are shown on page 9. In the *Write Cycle Timing 2* diagram, the data bus is shown as a hi-Z condition while the chip is write-enabled and before the required setup time. Although this is drawn to look like a mid-level voltage, it is recommended that all DQ pins comply with the minimum V_{IH}/V_{IL} operating levels.

Write access to the array begins on the falling edge of /WE after the memory cycle is initiated. The write access terminates on the deassertion of /WE or /CE, whichever comes first. A valid write operation requires the user to meet the access time specification prior to deasserting /WE or /CE. Data setup time indicates the interval during which data cannot change prior to the end of the write access.

Unlike other truly nonvolatile memory technologies, there is no write delay with F-RAM. Since the read and write access times of the underlying memory are the same, the user experiences no delay through the bus. The entire memory operation occurs in a single bus cycle. Data polling, a technique used with EEPROMs to determine if a write is complete, is unnecessary.

Page Mode Operation

The FM28V020 provides the user fast access to any data within a row element. Each row has eight column locations. An access can start anywhere within a row and other column locations may be accessed without the need to toggle the /CE pin. For page mode reads, once the first data byte is driven onto the bus, the column address inputs A(2:0) may be changed to a new value. A new data byte is then driven to the DQ pins. For page mode writes, the first write pulse defines the first write access. While the device is selected (/CE low), a subsequent write pulse along with a new column address provides a page mode write access.

Precharge Operation

The precharge operation is an internal condition in which the state of the memory is preparing for a new

access. Precharge is user-initiated by driving at least one of the chip enable signals to an inactive state. The chip enable must remain inactive for at least the minimum precharge time t_{PC} .

Precharge is also activated by changing the upper address A(14:3). The current row is first closed prior to accessing the new row. The device automatically detects an upper order address change which starts a

precharge operation, the new address is latched, and the new read data is valid within the t_{AA} address access time. Refer to the *Read Cycle Timing 1* diagram on page 9. Likewise a similar sequence occurs for write cycles. Refer to the *Write Cycle Timing 3* diagram on page 11. The rate at which random addresses can be issued is t_{RC} and t_{WC} , respectively.

Endurance

The FM28V020 is capable of being accessed at least 10^{14} times – reads or writes. An F-RAM memory operates with a read and restore mechanism. Therefore, an endurance cycle is applied on a row basis. The F-RAM architecture is based on an array of rows and columns. Rows are defined by A14-A3 and column addresses by A2-A0. The array is organized as 4K rows of 8-bytes each. The entire row is internally accessed once whether a single byte or all eight bytes are read or written. Each byte in the

row is counted only once in an endurance calculation if the addressing is contiguous in nature.

The user may choose to store CPU instructions and run them from a certain address space. The table below shows endurance calculations for 256-byte repeating loop, which includes a starting address and initial access, 7 page mode accesses, and a CE precharge. The number of bus clocks needed to complete an 8-byte read transaction is 1+7+1 or 9 clocks. The entire loop causes each byte to experience only one endurance cycle. F-RAM read and write endurance is virtually unlimited.

Table 1. Time to Reach 100 Trillion Cycles for Repeating 256-byte Loop

Bus Freq (MHz)	Bus Cycle Time (ns)	256-byte Transaction Time (μ s)	Endurance Cycles/sec.	Endurance Cycles/year	Years to Reach 10^{14} Cycles
10	100	28.8	34,720	1.09×10^{12}	91.7
5	200	57.6	17,360	5.47×10^{11}	182.8

SRAM Drop-In Replacement

The FM28V020 has been designed to be a drop-in replacement for standard asynchronous SRAMs. The device does not require /CE to toggle for each new address. /CE may remain low indefinitely while V_{DD} is applied. When /CE is low, the device automatically detects address changes and a new access begins. It also allows page mode operation at speeds up to 15MHz.

A typical application is shown in Figure 2. It shows a pullup resistor on /CE which will keep the pin high during power cycles assuming the MCU/MPU pin tri-states during the reset condition. The pullup resistor value should be chosen to ensure the /CE pin tracks V_{DD} yet a high enough value that the current drawn when /CE is low is not an issue.

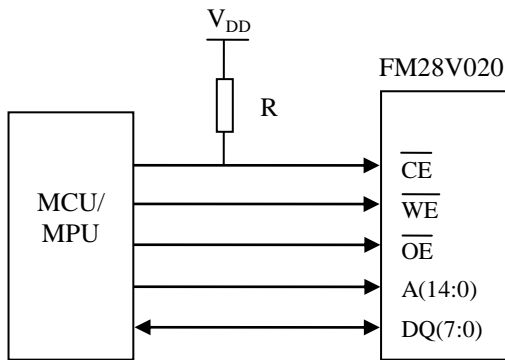


Figure 2. Typical Application using Pullup Resistor on /CE

For applications that require the lowest power consumption, the /CE signal should be active only during memory accesses. Due to the external pullup resistor, some supply current will be drawn while /CE is low. When /CE is high, the device draws no more than the maximum standby current I_{SB} .

Note that if /CE is grounded, the user must be sure /WE is not low at powerup or powerdown events. If the chip is enabled and /WE is low during power cycles, data corruption will occur. Figure 3 shows a pullup resistor on /WE which will keep the pin high during power cycles assuming the MCU/MPU pin tri-states during the reset condition. The pullup resistor value should be chosen to ensure the /WE pin tracks V_{DD} yet a high enough value that the current drawn

when /WE is low is not an issue. A 10Kohm resistor draws 330uA when /WE is low and $V_{DD}=3.3V$.

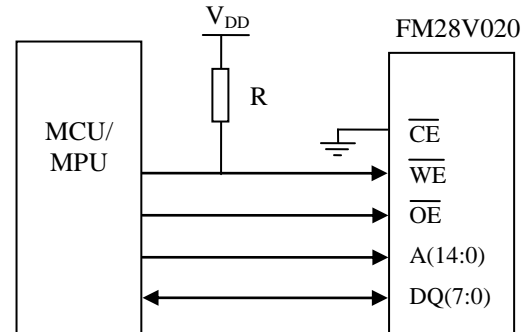


Figure 3. Use of Pullup Resistor on /WE

The FM28V020 is backward compatible with the 256Kbit FM18L08 device. Operating the FM28V020 with /CE toggling low on every address is perfectly acceptable.

PCB Layout Recommendations

A 0.1uF decoupling capacitor should be placed close to pin 28 (V_{DD}) and the ground side of the capacitor should be connected to either a ground plane or low impedance path back to pin 14 (V_{SS}). It is best to use a chip capacitor that has low ESR and has good high frequency characteristics.

If the controller drives the address and chip enable from the same timing edge, it is best to keep the address routes short and of equal length. A simple RC circuit may be inserted in the chip enable path to provide some delay and timing margin for the FM28V020's address setup time t_{AS} .

As a general rule, the layout designer may need to add series termination resistors to controller outputs that have fast transitions or routes that are > 15cm in length. This is only necessary if the edge rate is less than or equal to the round trip trace delay. Signal overshoot and ringback may be large enough to cause erratic device behavior. It is best to add a 50 ohm resistor (30 – 60 ohms) near the output driver (controller) to reduce such transmission line effects.

Electrical Specifications

Absolute Maximum Ratings

Symbol	Description	Ratings
V_{DD}	Power Supply Voltage with respect to V_{SS}	-1.0V to +4.5V
V_{IN}	Voltage on any signal pin with respect to V_{SS}	-1.0V to +4.5V and $V_{IN} < V_{DD} + 1V$
T_{STG}	Storage Temperature	-55°C to +125°C
T_{LEAD}	Lead Temperature (Soldering, 10 seconds)	260° C
V_{ESD}	Electrostatic Discharge Voltage - Human Body Model (AEC-Q100-002 Rev. E) - Charged Device Model (AEC-Q100-011 Rev. B) - Machine Model (AEC-Q100-003 Rev. E)	2kV 1.25kV 200V
	Package Moisture Sensitivity Level	MSL-2 (SOIC) MSL-3 (TSOP)

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only, and the functional operation of the device at these or any other conditions above those listed in the operational section of this specification is not implied. Exposure to absolute maximum ratings conditions for extended periods may affect device reliability.

DC Operating Conditions ($T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$, $V_{DD} = 2.0V$ to $3.6V$ unless otherwise specified)

Symbol	Parameter	Min	Typ	Max	Units	Notes
V_{DD}	Power Supply	2.0	3.3	3.6	V	
I_{DD}	V_{DD} Supply Current		5	8	mA	1
I_{SB}	Standby Current – CMOS		90	150	μA	2
I_{LI}	Input Leakage Current			± 1	μA	3
I_{LO}	Output Leakage Current			± 1	μA	3
V_{IH}	Input High Voltage	$0.7 V_{DD}$		$V_{DD} + 0.3$	V	
V_{IL}	Input Low Voltage	-0.3		$0.3 V_{DD}$	V	
V_{OH1}	Output High Voltage ($I_{OH} = -1\text{ mA}$, $V_{DD}=2.7V$)	2.4			V	
V_{OH2}	Output High Voltage ($I_{OH} = -100\ \mu\text{A}$)	$V_{DD}-0.2$			V	
V_{OL1}	Output Low Voltage ($I_{OL} = 1\text{ mA}$, $V_{DD}=2.7V$)			0.4	V	
V_{OL2}	Output Low Voltage ($I_{OL} = 150\ \mu\text{A}$)			0.2	V	

Notes

- $V_{DD} = 3.6V$, /CE cycling at minimum cycle time. All inputs at CMOS levels (0.2V or $V_{DD}-0.2V$), all DQ pins unloaded.
- $V_{DD} = 3.6V$, /CE at V_{DD} , All other pins at CMOS levels (0.2V or $V_{DD}-0.2V$).
- V_{IN} , V_{OUT} between V_{DD} and V_{SS} .

Read Cycle AC Parameters ($T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$, $C_L = 30\text{ pF}$, $V_{DD} = 2.0\text{V}$ to 3.6V unless otherwise specified)

Symbol	Parameter	Min	Max	Units	Notes
t_{RC}	Read Cycle Time	140	-	ns	
t_{CE}	Chip Enable Access Time	-	70	ns	
t_{AA}	Address Access Time	-	140	ns	
t_{OH}	Output Hold Time	20	-	ns	
t_{AAP}	Page Mode Address Access Time	-	40	ns	
t_{OHP}	Page Mode Output Hold Time	3	-	ns	
t_{CA}	Chip Enable Active Time	70	-	ns	
t_{PC}	Precharge Time	70	-	ns	
t_{AS}	Address Setup Time (to /CE low)	0	-	ns	
t_{AH}	Address Hold Time (/CE-controlled)	70	-	ns	
t_{OE}	Output Enable Access Time	-	20	ns	3
t_{HZ}	Chip Enable to Output High-Z	-	10	ns	1
t_{OHZ}	Output Enable High to Output High-Z	-	10	ns	1

Write Cycle AC Parameters ($T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$, $V_{DD} = 2.0\text{V}$ to 3.6V unless otherwise specified)

Symbol	Parameter	Min	Max	Units	Notes
t_{WC}	Write Cycle Time	140	-	ns	
t_{CA}	Chip Enable Active Time	70	-	ns	
t_{CW}	Chip Enable to Write Enable High	70	-	ns	
t_{PC}	Precharge Time	70	-	ns	
t_{PWC}	Page Mode Write Enable Cycle Time	35	-	ns	
t_{WP}	Write Enable Pulse Width	18	-	ns	
t_{AS}	Address Setup Time (to /CE low)	0	-	ns	
t_{AH}	Address Hold Time (/CE-controlled)	70	-	ns	
t_{ASP}	Page Mode Address Setup Time (to /WE low)	5	-	ns	
t_{AHP}	Page Mode Address Hold Time (to /WE low)	20	-	ns	
t_{WLC}	Write Enable Low to /CE High	25	-	ns	
t_{WLA}	Write Enable Low to A(14:3) Change	25	-	ns	
t_{AWH}	A(14:3) Change to Write Enable High	140	-	ns	
t_{DS}	Data Input Setup Time	15	-	ns	
t_{DH}	Data Input Hold Time	0	-	ns	
t_{WZ}	Write Enable Low to Output High Z	-	10	ns	1
t_{WX}	Write Enable High to Output Driven	5	-	ns	1
t_{WS}	Write Enable to /CE Low Setup Time	0	-	ns	1,2
t_{WH}	Write Enable to /CE High Hold Time	0	-	ns	1,2

Notes

- 1 This parameter is characterized but not 100% tested.
- 2 The relationship between /CE and /WE determines if a /CE- or /WE-controlled write occurs.
- 3 For $V_{DD} < 2.7\text{V}$, t_{OE} max is 25ns.

Power Cycle Timing ($T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$, $V_{DD} = 2.0\text{V}$ to 3.6V unless otherwise specified)

Symbol	Parameter	Min	Max	Units	Notes
t_{VR}	V_{DD} Rise Time	50	-	$\mu\text{s/V}$	1
t_{VF}	V_{DD} Fall Time	100	-	$\mu\text{s/V}$	1
t_{PU}	Power Up (V_{DD} min) to First Access Time	250	-	μs	
t_{PD}	Last Access to Power Down (V_{DD} min)	0	-	μs	

Notes

- 1 Slope measured at any point on V_{DD} waveform.

Data Retention ($V_{DD} = 2.0V$ to $3.6V$, $+85^{\circ}C$)

Parameter	Min	Max	Units	Notes
Data Retention	10	-	Years	

Capacitance ($T_A = 25^{\circ}C$, $f=1$ MHz, $V_{DD} = 3.3V$)

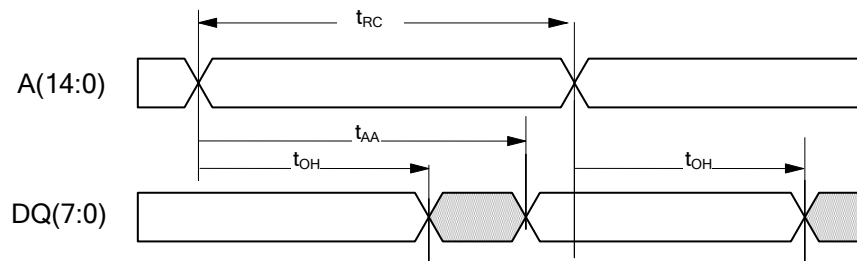
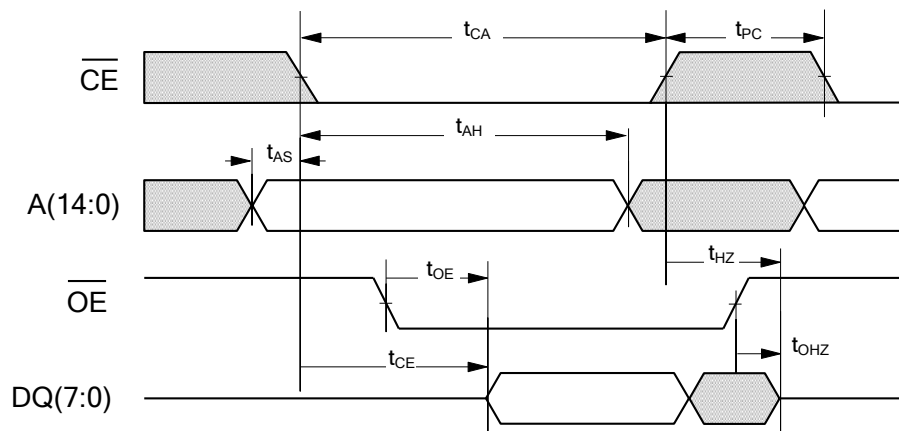
Symbol	Parameter	Min	Max	Units	Notes
$C_{I/O}$	Input/Output Capacitance (DQ)	-	8	pF	1
C_{IN}	Input Capacitance	-	6	pF	1

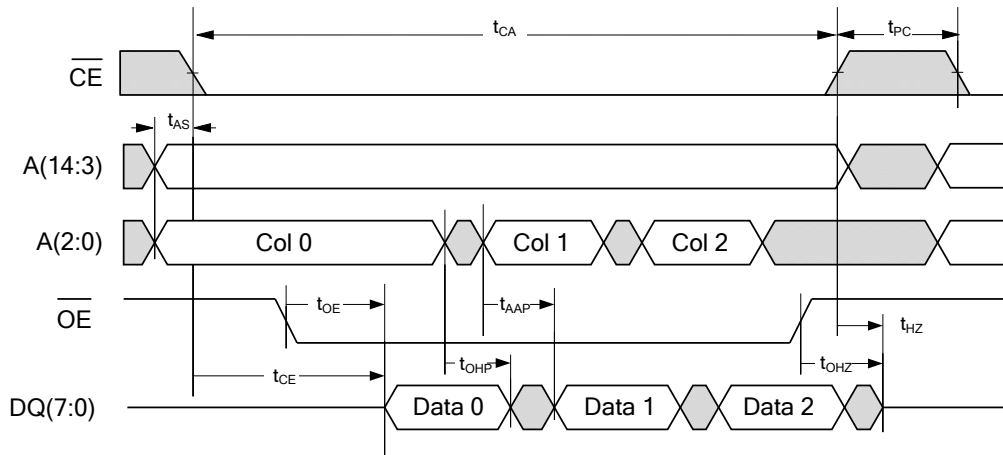
Notes

- This parameter is characterized and not 100% tested.

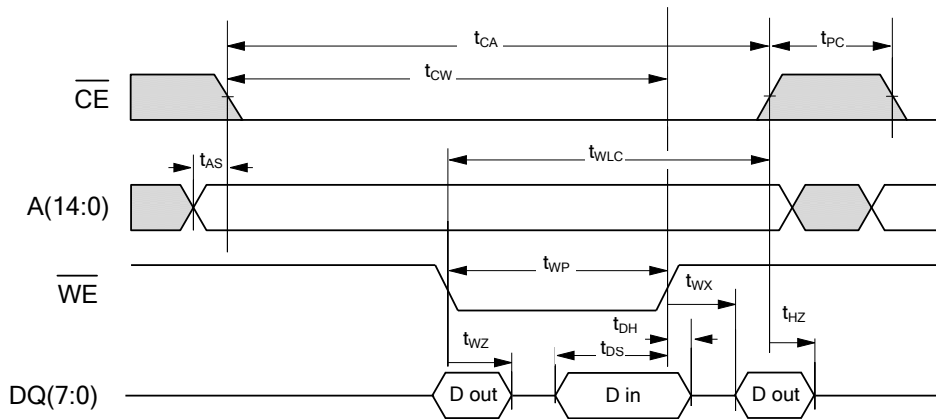
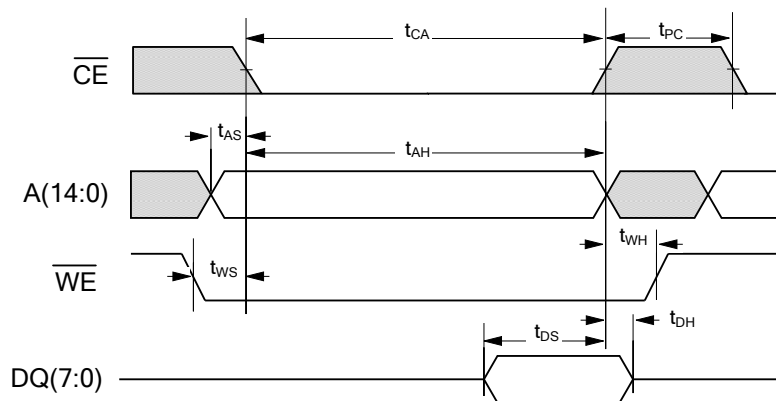
AC Test Conditions

Input Pulse Levels	0 to 3V
Input rise and fall times	3 ns
Input and output timing levels	1.5V
Output Load Capacitance	30 pF

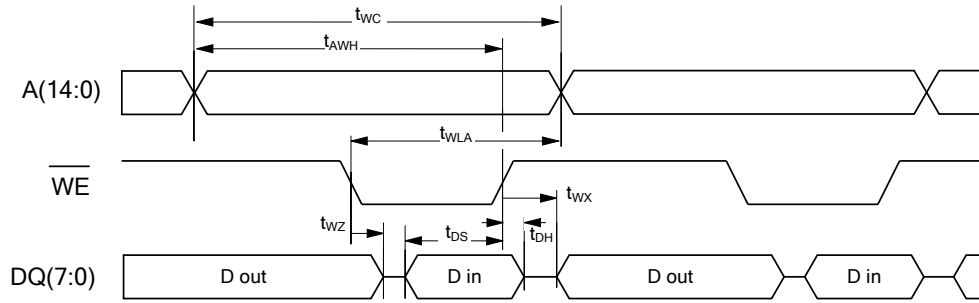
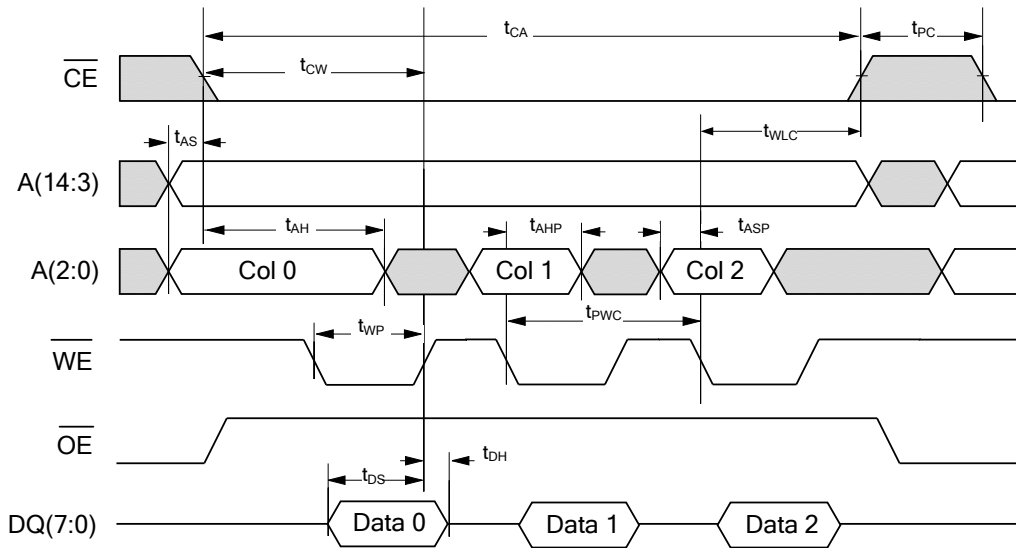
Read Cycle Timing 1 ($/\overline{CE}$ low, $/\overline{OE}$ low)

Read Cycle Timing 2 ($/\overline{CE}$ -controlled)


Page Mode Read Cycle Timing


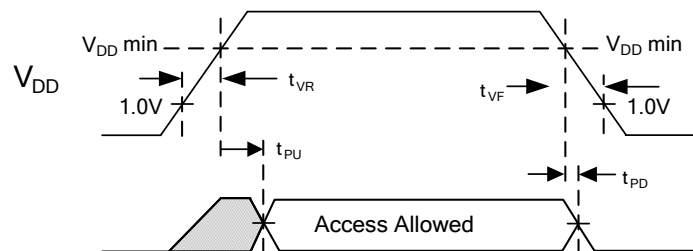
Although sequential column addressing is shown, it is not required.

Write Cycle Timing 1 (/WE-Controlled) Note: \overline{OE} is low only to show effect of \overline{WE} on DQ pins

Write Cycle Timing 2 (/CE-Controlled)


NOTE: See Write Operation section for detailed description (page 4).

Write Cycle Timing 3 (/CE low) Note: /OE is low only to show effect of /WE on DQ pins

Page Mode Write Cycle Timing


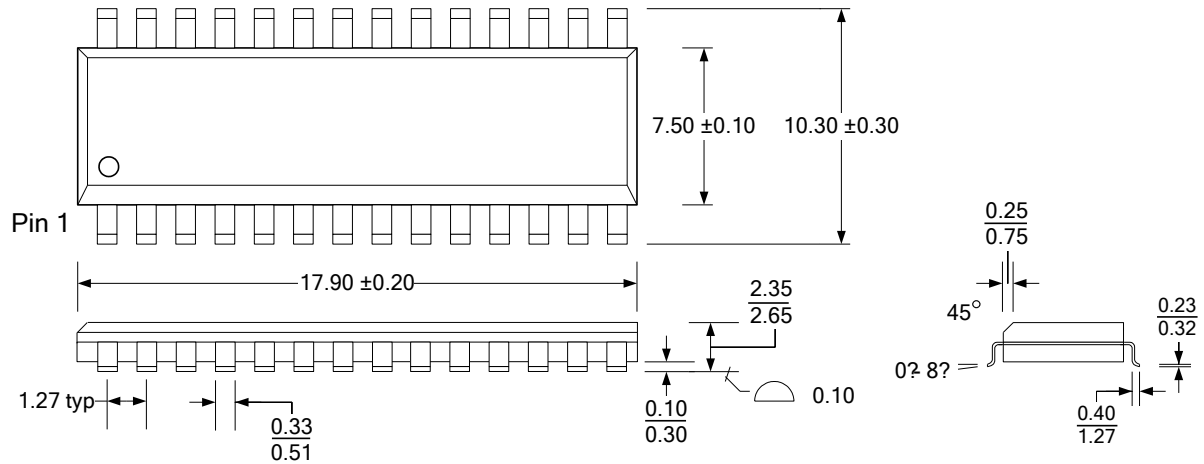
Although sequential column addressing is shown, it is not required.

Power Cycle Timing


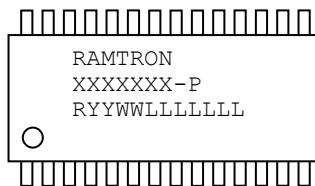
Mechanical Drawing

28-pin SOIC (JEDEC MS-013D Variation AE)

All dimensions in millimeters



SOIC Package Marking Scheme



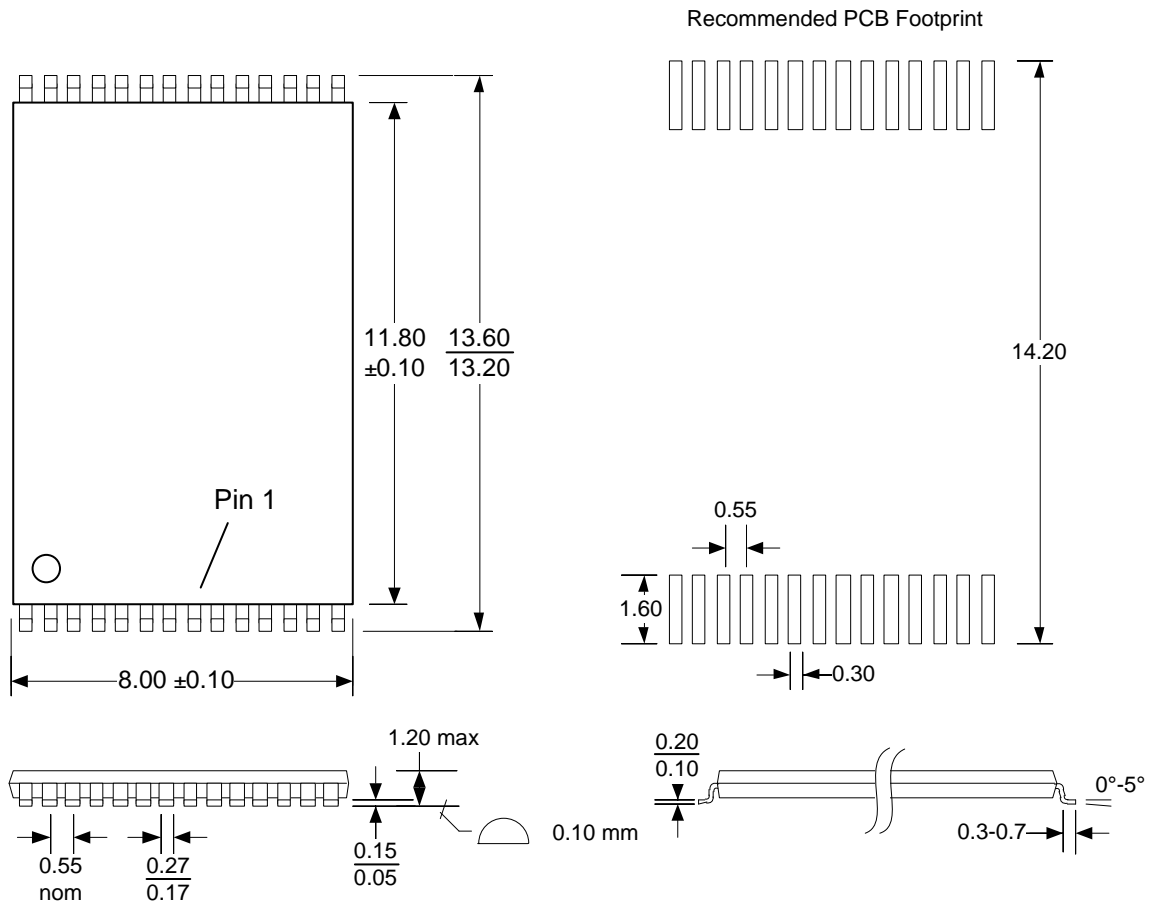
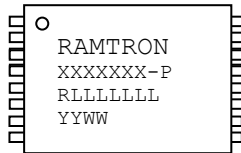
Legend:

XXXXXX= part number, P= package type (SG=SOIC "Green")
 R=Rev, YY=year, WW=work week, LLLLLL= lot code

Example: FM28V020, "Green"/RoHS SOIC package,
 Rev. A, Year 2010, Work Week 18, Lot code 9482296

```

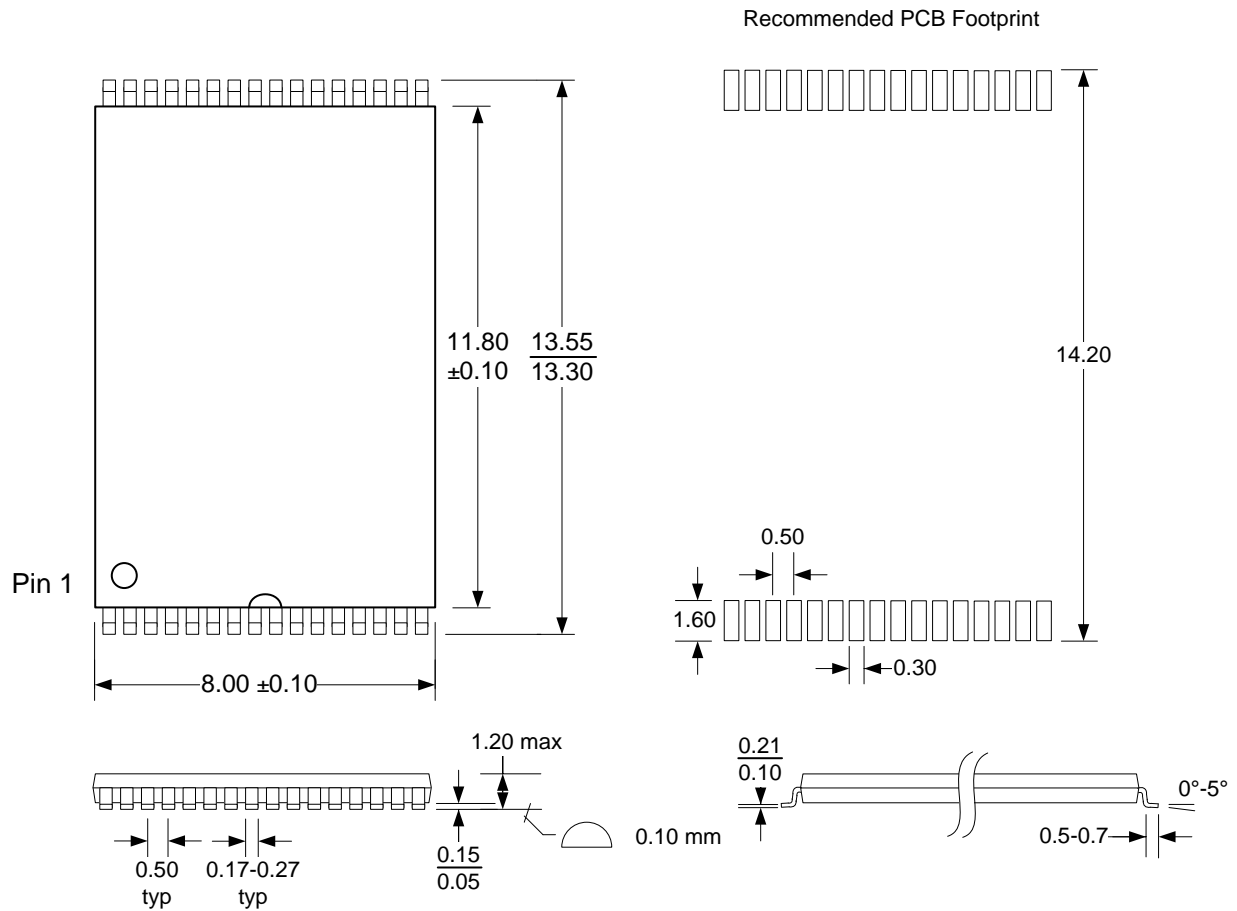
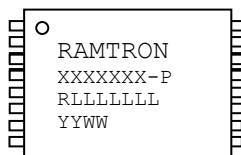
RAMTRON
FM28V020-SG
A10189482296G
  
```

28-pin Shrunk TSOP-I (8.0 x 13.4 mm)
All dimensions in millimeters
Complies with JEDEC MO-183

TSOP Package Marking Scheme

Legend:

XXXXXX= part number, P= package/option (TG=TSOP “Green”)
 R=rev code, YY=year, WW=work week, LLLLLL= lot code

Example: FM28V020-T28G, “Green” 28-lead TSOP package,
 Rev. A, Year 2012, Work Week 18, Lot 9482296

RAMTRON
 FM28V020T28G
 A9482296TG
 1218

32-pin Shrunk TSOP-I (8.0 x 13.4 mm)
All dimensions in millimeters

TSOP Package Marking Scheme

Legend:

XXXXXX= part number, P= package/option (TG=TSOP “Green”)
 R=rev code, YY=year, WW=work week, LLLLLL= lot code

Example: FM28V020-TG, “Green” TSOP package,
 Rev. A, Year 2010, Work Week 18, Lot 9482296

```

RAMTRON
FM28V020-TG
A9482296TG
1018

```

Revision History

Revision	Date	Summary
1.0	4/15/2009	Initial release.
1.1	9/8/2009	Added TSOP package and MSL rating. Expanded explanation of precharge operation. Updated lead temperature rating in Abs Max table.
1.2	4/22/2010	Updated MSL rating on SOIC package.
2.0	5/25/2010	Changed to Pre-Production status. Added ESD ratings. Changed part marking scheme.
2.1	6/10/2011	Changed AC timing specs. Changed V_{OL1} test condition. Changed endurance section.

Document History

Document Title: FM28V020 256Kbit (32Kx8) Byte-wide F-RAM Memory

Document Number: 001-86204

Revision	ECN	Orig. of Change	Submission Date	Description of Change
**	3912932	GVCH	02/25/2013	New Spec
*A	3924836	GVCH	03/07/2013	Changed to Production status Added 28-pin TSOP package type Changed I_{DD} limit min spec from 7mA to 5mA and max spec from 12mA to 8mA. Read Cycle AC Parameters: Changed t_{AAP} spec value from 60 to 40ns and t_{OE} spec value from 15 ns to 20 ns Write Cycle AC Parameters: Changed t_{PWC} spec value from 30 to 35 ns and t_{AHP} spec value from 15 to 20ns

Sales, Solutions, and Legal Information

Worldwide Sales and Design Support

Cypress maintains a worldwide network of offices, solution centers, manufacturer's representatives, and distributors. To find the office closest to you, visit us at [Cypress Locations](#).

Products

Automotive	cypress.com/go/automotive
Clocks & Buffers	cypress.com/go/clocks
Interface	cypress.com/go/interface
Lighting & Power Control	cypress.com/go/powerpsoc cypress.com/go/plc
Memory	cypress.com/go/memory
PSoC	cypress.com/go/psoc
Touch Sensing	cypress.com/go/touch
USB Controllers	cypress.com/go/usb

PSoC[®] Solutions

psoc.cypress.com/solutions
PSoC 1 | PSoC 3 | PSoC 5

Cypress Developer Community

[Community](#) | [Forums](#) | [Blogs](#) | [Video](#) | [Training](#)

Technical Support

cypress.com/go/support

RAMTRON is a registered trademark and NoDelay™ is a trademark of Cypress Semiconductor Corp. All other trademarks or registered trademarks referenced herein are the property of their respective owners.

© Cypress Semiconductor Corporation, 2011-2013. The information contained herein is subject to change without notice. Cypress Semiconductor Corporation assumes no responsibility for the use of any circuitry other than circuitry embodied in a Cypress product. Nor does it convey or imply any license under patent or other rights. Cypress products are not warranted nor intended to be used for medical, life support, life saving, critical control or safety applications, unless pursuant to an express written agreement with Cypress. Furthermore, Cypress does not authorize its products for use as critical components in life-support systems where a malfunction or failure may reasonably be expected to result in significant injury to the user. The inclusion of Cypress products in life-support systems application implies that the manufacturer assumes all risk of such use and in doing so indemnifies Cypress against all charges.

This Source Code (software and/or firmware) is owned by Cypress Semiconductor Corporation (Cypress) and is protected by and subject to worldwide patent protection (United States and foreign), United States copyright laws and international treaty provisions. Cypress hereby grants to licensee a personal, non-exclusive, non-transferable license to copy, use, modify, create derivative works of, and compile the Cypress Source Code and derivative works for the sole purpose of creating custom software and or firmware in support of licensee product to be used only in conjunction with a Cypress integrated circuit as specified in the applicable agreement. Any reproduction, modification, translation, compilation, or representation of this Source Code except as specified above is prohibited without the express written permission of Cypress.

Disclaimer: CYPRESS MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARD TO THIS MATERIAL, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE. Cypress reserves the right to make changes without further notice to the materials described herein. Cypress does not assume any liability arising out of the application or use of any product or circuit described herein. Cypress does not authorize its products for use as critical components in life-support systems where a malfunction or failure may reasonably be expected to result in significant injury to the user. The inclusion of Cypress' product in a life-support systems application implies that the manufacturer assumes all risk of such use and in doing so indemnifies Cypress against all charges.

Use may be limited by and subject to the applicable Cypress software license agreement.

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9